

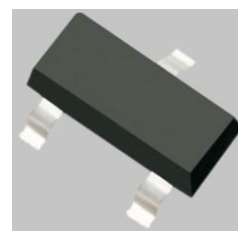
# BC807/BC808-16/-25/-40

## PNP Transistor

### Features

- ◆ For switching, AF driver and amplifier applications
- ◆ These transistors are subdivided into three groups -16, -25 and -40, according to their current gain. As complementary types the NPN transistors BC817 and BC818 are recommended

SOT-23



1 Base 2. Emitter 3. Collector

### Absolute Maximum Ratings (T<sub>A</sub>=25°C, unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector Base Voltage	BC807 BC808 V <sub>CB0</sub>	-50 -30	V
Collector Emitter Voltage	BC807 BC808 V <sub>CEO</sub>	-45 -25	V
Emitter Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current	I <sub>C</sub>	-0.5	A
Power Dissipation	P <sub>C</sub>	0.3	W
Operation Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

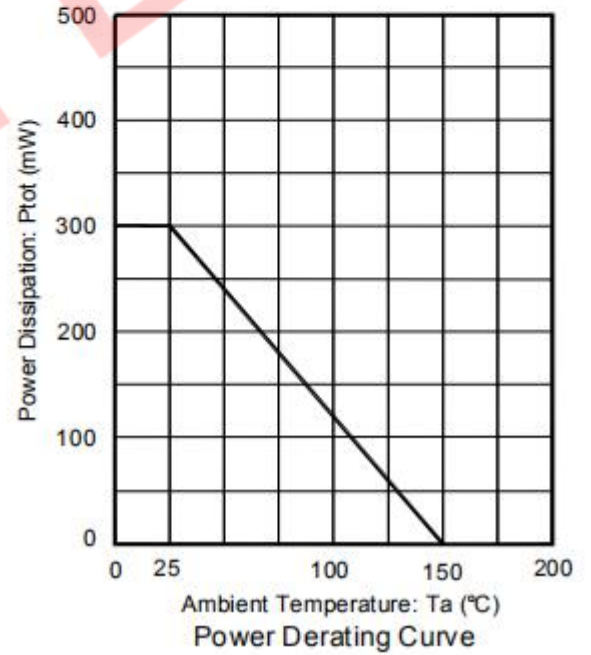
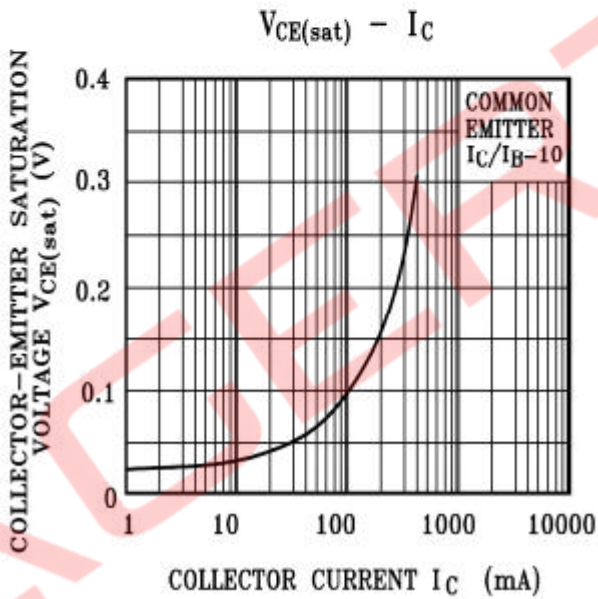
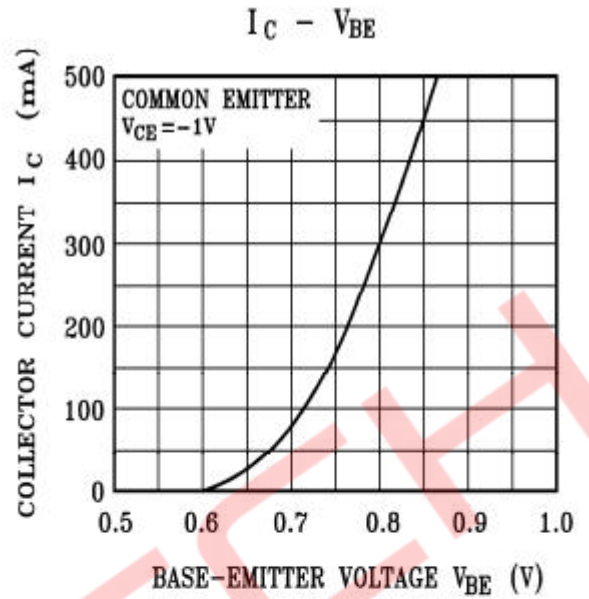
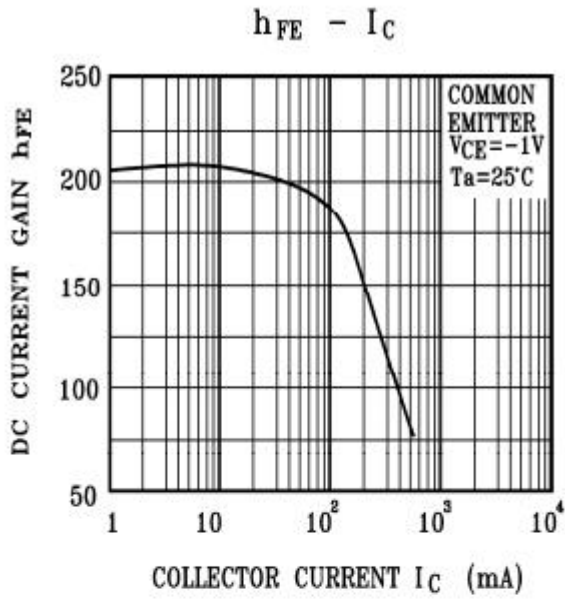
### Electrical Characteristics (T<sub>A</sub>=25 °C, unless otherwise noted)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> = -20V			-100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -5V			-100	nA
DC current gain	BC807/BC808-16 h <sub>FE1</sub>	V <sub>CE</sub> = -1V, I <sub>C</sub> = -100mA	100		250	
	BC807/BC808-25 h <sub>FE2</sub>		160		400	
	BC807/BC808-40 h <sub>FE3</sub>		250		600	
	h <sub>FE4</sub>		40			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA			-0.7	V
Base-emitter saturation voltage	V <sub>BE(on)</sub>	I <sub>C</sub> = -500mA, V <sub>CE</sub> = -1V			-1.2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -10mA, f = 50MHz	80			MHZ
Collector Base Capacitance	C <sub>cbo</sub>	V <sub>CB</sub> = -10V, f = 1MHz		9		pF

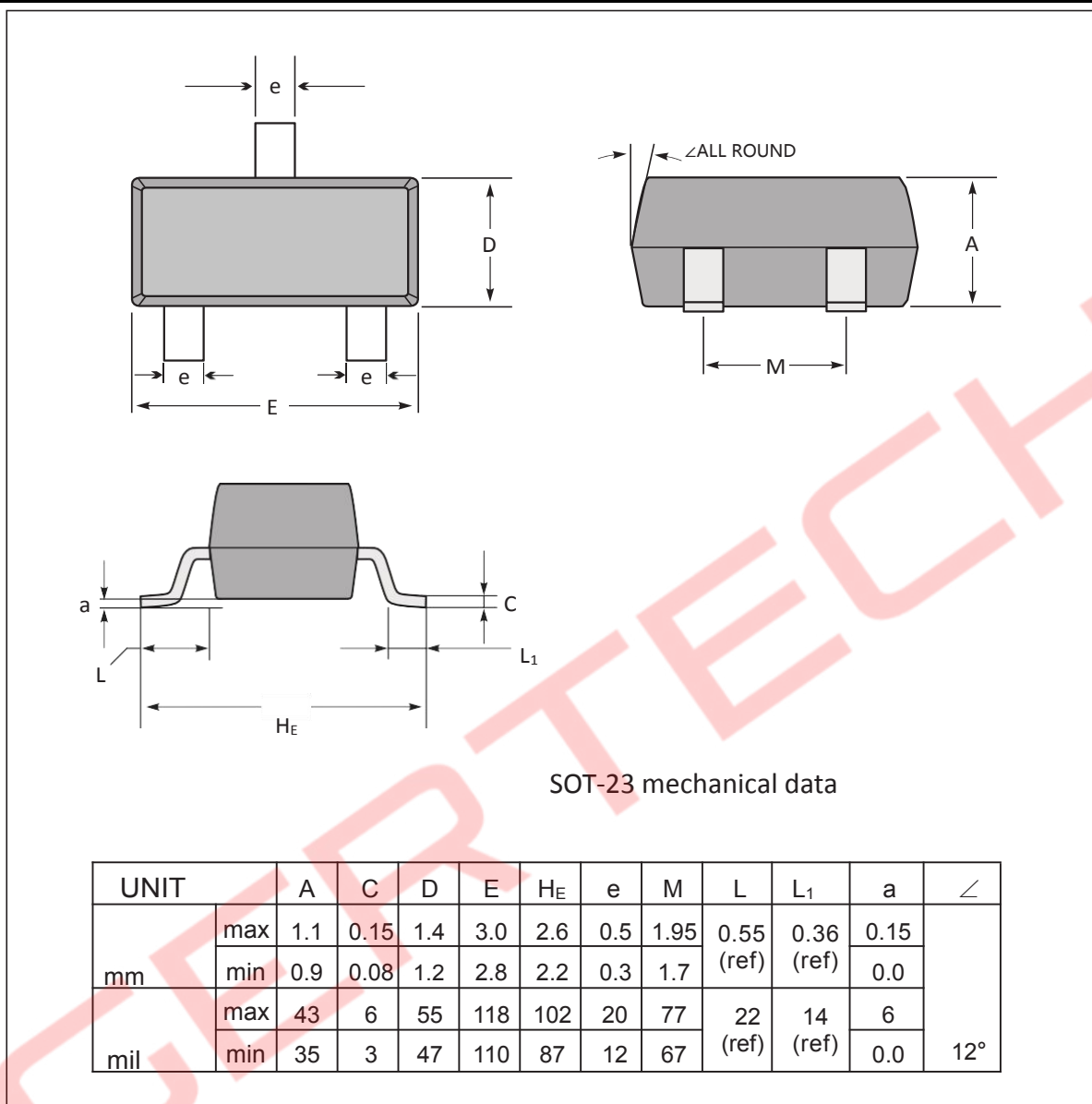
### Marking

RANK	BC807-16	BC807-25	BC807-40
Marking	5CR	5CS	5CT
RANK	BC808-16	BC808-25	BC808-40
Marking	5CW	5CX	5CY

## Typical Characteristics Curves



## Package Outline



### The recommended mounting pad size

